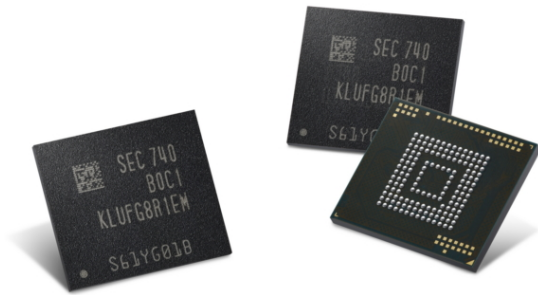


Samsung Produces 512GB eUFS Storage

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Samsung starts mass production of the first 512GB embedded Universal Flash Storage (eUFS) solutions, paving the way for mobile devices with even larger storage capacities.



The storage components consist of eight 64-layer 512Gb Samsung V-NAND chips paired with a controller chip. The result is double the density of the previous 48-layer V-NAND-based 256GB eUFS, while taking the same amount of space within a device. Also included are a power management system minimising energy consumption and a faster mapping process for the conversion of logical block addresses to those of physical blocks.

Samsung claims such storage allows a smartphone to store 130 4K UHD video clips of 10 minute duration, a tenfold increase over a 64GB eUFS, with performance reaching 42000 IOPS read and 40000 IOPS write for random operations, 400x faster than conventional microSD cards.

The first device carrying 512GB eUFS storage should hit the market early next year, with a probable debut at CES 2018.

Go [Samsung Starts Producing First 512GB eUFS for Next-Generation Mobile Devices](#)